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Date Submitted: March 11, 2008

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Sheet 1 of 1

Complete if Known

Application Number 10/538,739
Filing Date 12/15/2003
First Named Inventor Yasuhiro OKAMOTO
Art Unit 2814
Examiner Name Sarah Kate Salerno
Attorney Docket Number 029437-0108

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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UNPUBLISHED U.S. PATENT APPLICATION DOCUMENTS

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FOREIGN PATENT DOCUMENTS

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		Country Code ² Number ³ Kind Code ⁴ (if known)				
	B1	JP 2002-359256A	12-13-2002	FUJITSU LTD.		

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ^o
	B2	Li et al., "High breakdown voltage GaN HFET with field plate," Electronics Letters, February 1, 2001, Vol. 37, No. 3, pp. 196-197.	
	B3	TAN et al., "The Effect of Dielectric Stress on the Electrical Characteristics of AlGaIn/GaN Heterostructure Field-Effect Transistors (HFETs)," The 10 th IEEE International Symposium on Electron Devices for Microwave and Optoelectronic Applications, November 2002, pp. 130-135.	
	B4	ZHANG, N.Q. et al., "Effects of surface traps on breakdown voltage and switching speed of GaN power switching HEMTs," 2001 IEEE, pp. 25.5.1-25.5.4.	

Examiner
Signature

/Sarah Salerno/

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